

Silicon PNP Power Transistors

2SB941 2SB941A

DESCRIPTION

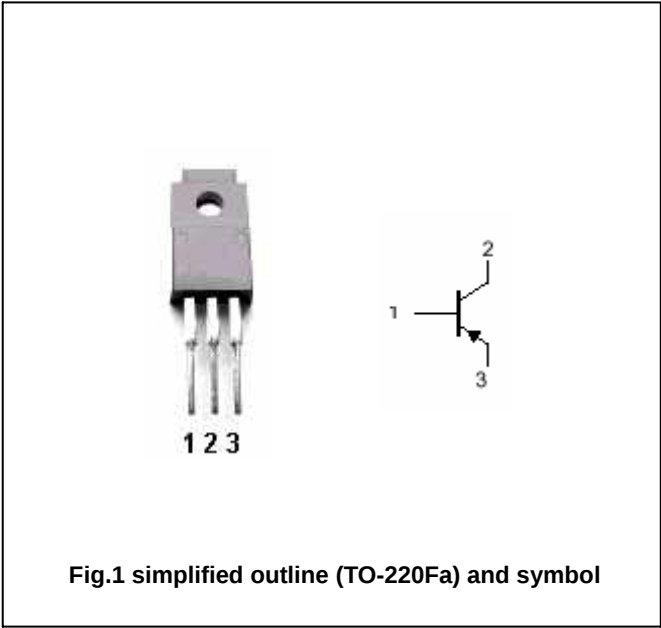
- With TO-220Fa package
- Low collector saturation voltage
- Complementary to type 2SD1266/1266A

APPLICATIONS

- For low-frequency power amplification

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SB941	Open emitter	-60	V
		2SB941A		-80	
V _{CEO}	Collector-emitter voltage	2SB941	Open base	-60	V
		2SB941A		-80	
V _{EBO}	Emitter-base voltage		Open collector	-5	V
I _C	Collector current			-3	A
I _{CM}	Collector current-peak			-5	A
P _C	Collector power dissipation		T _a =25	2	W
			T _C =25	35	
T _j	Junction temperature			150	
T _{stg}	Storage temperature			-55~150	

Silicon PNP Power Transistors

2SB941 2SB941A

CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO}	Collector-emitter voltage	2SB941	I _C =-30mA, I _B =0	-60			V
		2SB941A		-80			
V _{CEsat}	Collector-emitter saturation voltage		I _C =-3A, I _B =-0.375A			-1.2	V
V _{BE}	Base-emitter voltage		I _C =-3A; V _{CE} =-4V			-1.8	V
I _{EBO}	Emitter cut-off current		V _{EB} =-5V; I _C =0			-1	mA
I _{CEO}	Collector cut-off current	2SB941	V _{CE} =-30V; I _B =0			-0.3	mA
		2SB941A	V _{CE} =-60V; I _B =0				
I _{CES}	Collector cut-off current	2SB941	V _{CE} =-60V; V _{BE} =0			-0.2	mA
		2SB941A	V _{CE} =-80V; V _{BE} =0				
h _{FE-1}	DC current gain		I _C =-1A; V _{CE} =-4V	70		250	
h _{FE-2}	DC current gain		I _C =-3A; V _{CE} =-4V	10			
f _T	Transition frequency		I _C =0.5A; V _{CE} =-10V, f=10MHz		30		MHz

Switching times

t _{on}	Turn-on time	I _C =-1A I _{B1} =-0.1A, I _{B2} =0.1A		0.5		μs
t _{stg}	Storage time			1.2		μs
t _f	Fall time			0.3		μs

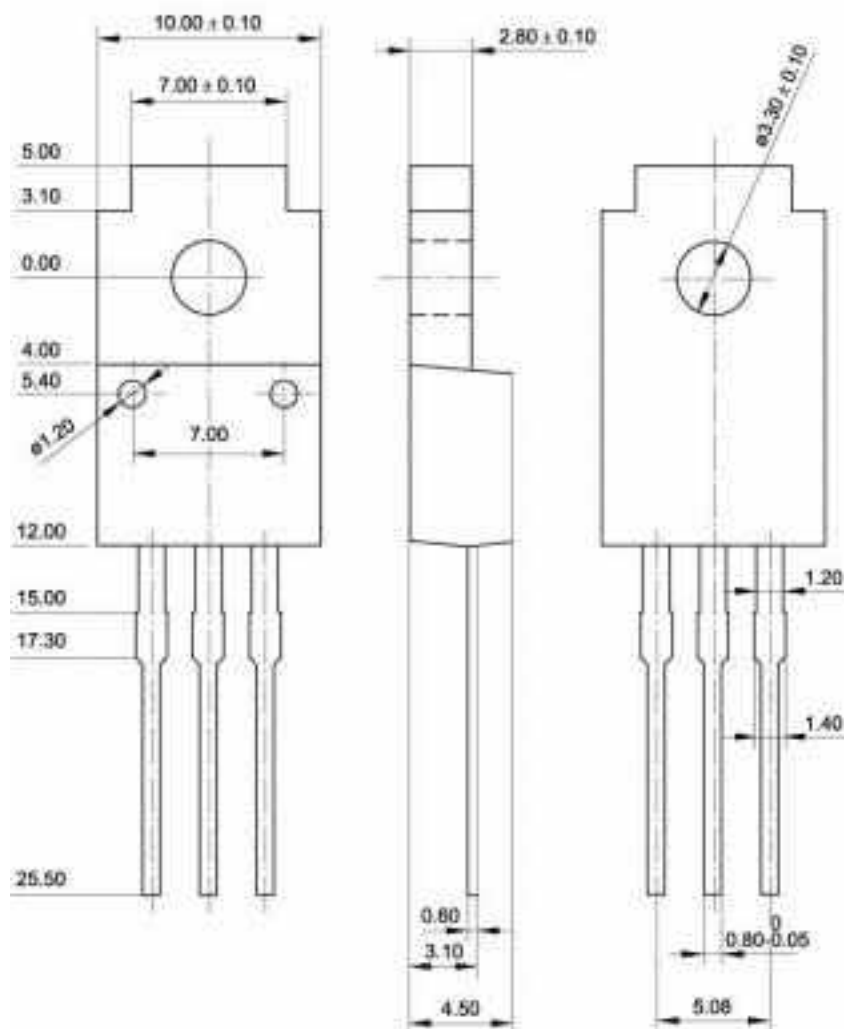
◆ h_{FE-1} Classifications

Q	P
70-150	120-250

Silicon PNP Power Transistors

2SB941 2SB941A

PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)

Silicon PNP Power Transistors

2SB941, 2SB941A

